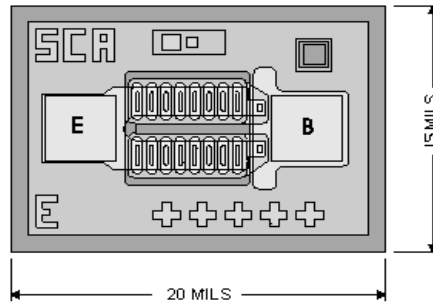


**Chip Type 2C3866A**  
**Geometry 1007**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N3866, 2N3866A**



[Request Quotation](#)

Chip type **2C3866A** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

[2N3866A](#), 2N3866, 2N3866AUB, SD3866A, SD3866AF, SQ3866A, SQ3866AF

**Product Summary:**

**APPLICATIONS:** Designed for amplifier, frequency multiplier and oscillator applications. Suitable for output, driver and predriver stages in VHF and UHF equipment.

**Features: Special Characteristics:**

$f_t = 950 \text{ MHz (type) at } 50 \text{ mA/15V}$

Mechanical Specifications		
Metallization	Top	Al - 15 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	3.4 mils x 3.0 mils
	Base	3.4 mils x 3.0 mils
Die Thickness	8 mils nominal	
Chip Area	15 mils x 20 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 5.0 \text{ mA}$	30	---	V dc
$BV_{CBO}$	$I_C = 100 \mu\text{A}$	55	---	V dc
$BV_{CER}$	$I_C = 5.0 \text{ mA}, R_{BE} = 10 \text{ Ohms}$	55	---	V dc
$BV_{EBO}$	$I_E = 100 \mu\text{A}$	3.5	---	V dc
$I_{CEO}$	$V_{CE} = 28 \text{ V}, V_{EB} = 2.0 \text{ V}$	---	20	$\mu\text{A}$
$h_{FE1}$	$I_C = 360 \text{ mA dc}, V_{CE} = 5.0 \text{ V}$	5.0	---	---
$h_{FE2}$	$I_C = 50 \text{ mA dc}, V_{CE} = 5.0 \text{ V}$	10	200	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.*